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(54) **Title:** PHASE CHANGE MEMORY STRUCTURES AND METHODS

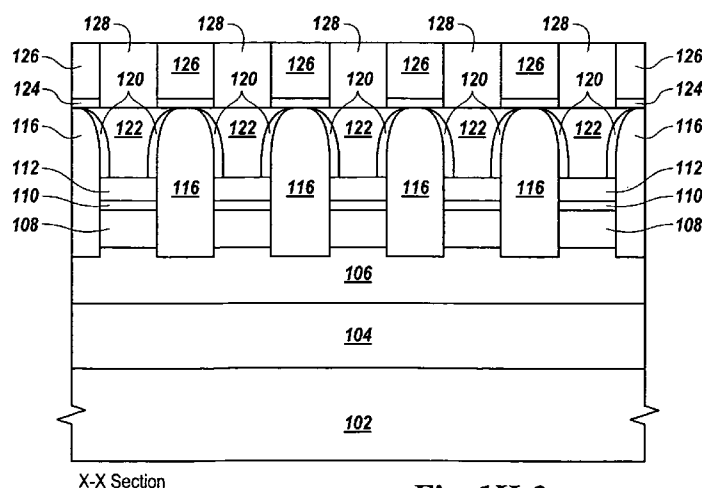


Fig. 1H-2

(57) **Abstract:** Methods, devices, and systems associated with phase change material memory are described herein. In one or more embodiments, a method of forming a phase change material memory cell includes forming a number of memory structure regions, wherein the memory structure regions include a bottom electrode material and a sacrificial material, forming a number of insulator regions between the number of memory structure regions, forming a number of openings between the number of insulator regions and forming a contoured surface on the number of insulator regions by removing the sacrificial material and a portion of the number of insulator regions, forming a number of dielectric spacers on the number of insulator regions, forming a contoured opening between the number of insulator regions and exposing the bottom electrode material by removing a portion of the number of dielectric spacers, and forming a phase change material in the opening between the number of insulator regions.